STP75N75F4

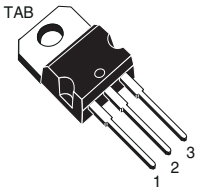
N-channel 75 V, 0.0092 Ω typ., 78 A STripFET™ DeepGATE™ Power MOSFET in a TO-220 package

Datasheet — production data

Features

Type	V_{DSS}	$R_{DS(on)}$ max	I_D
STP75N75F4	75 V	< 0.011 Ω	78 A

- N-channel enhancement mode
- 100% avalanched rated
- Low gate charge
- Very low on-resistance



TO-220

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using ST's STripFET™ DeepGATE™ technology. The device has a new gate structure and is specially designed to minimize on-state resistance to provide superior switching performance.

Figure 1. Internal schematic diagram

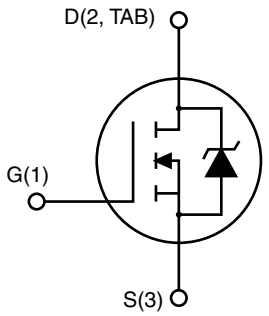


Table 1. Device summary

Order codes	Marking	Package	Packaging
STP75N75F4	75N75F4	TO-220	Tube

This is information on a product in full production. www.st.com

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2.1 Electrical characteristics (curves) 6

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	75	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at T_C = 25 °C	78	A
I_D	Drain current (continuous) at T_C = 100 °C	55	A
I_{DM} (1)	Drain current (pulsed)	312	A
P_{TOT}	Total dissipation at T_C = 25 °C	150	W
	Derating factor	1	W/°C
E_{AS} (2)	Single pulse avalanche energy	185	mJ
T_{stg}	Storage temperature	– 55 to 175	°C
T_j	Operating junction temperature		

1. Pulse width limited by safe operating area
2. Starting T_j = 25 °C, I_D= 35 A, V_{DD}= 50 V

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	1	°C/W
$R_{thj\text{-}a}$	Thermal resistance junction-ambient max	62.5	°C/W

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	I_D = 250 µA, V_{GS} = 0	75			V
I_{DSS}	Zero gate voltage Drain current (V_{GS} = 0)	V_{DS} = 75 V V_{DS} = 75 V,T_C=125 °C			1 100	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 39 A		0.0092	0.011	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0	-	5015	-	pF
C_{oss}	Output capacitance			382		pF
C_{rss}	Reverse transfer capacitance			218		pF
Q_g	Total gate charge	V_{DD} = 37.5 V, I_D = 78 A, V_{GS} = 10 V *(see Figure 14)*	-	76	-	nC
Q_{gs}	Gate-source charge			23		nC
Q_{gd}	Gate-drain charge			18.5		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 37.5 V, I_D = 39 A R_G = 4.7 Ω V_{GS} = 10 V *(see Figure 13)*	-	25	-	ns
t_r	Rise time			33		ns
$t_{d(off)}$	Turn-off-delay time		-	61	-	ns
t_f	Fall time			14		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		78	A
I_{SDM} (1)	Source-drain current (pulsed)		-		312	A
V_{SD} (2)	Forward on voltage	I_{SD} = 78 A, V_{GS} = 0	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 78 A, V_{DD} = 60 V di/dt = 100 A/µs, T_j = 150 °C *(see Figure 15)*	-	67 183 5.5		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

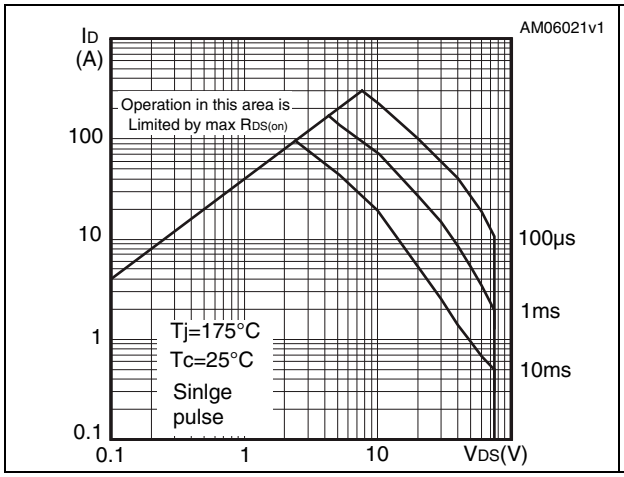


Figure 3. Thermal impedance

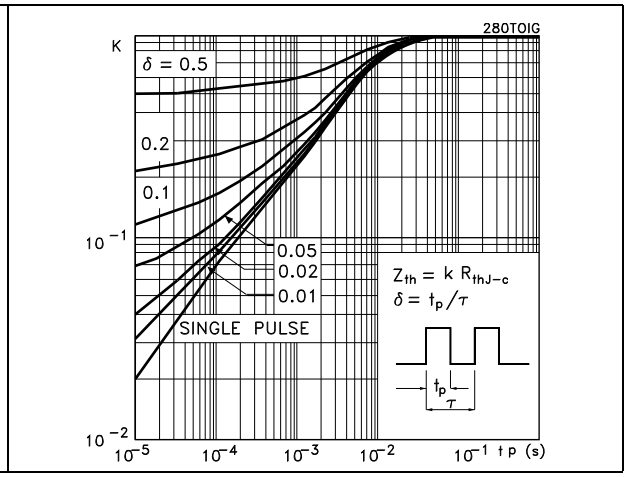


Figure 4. Output characteristics

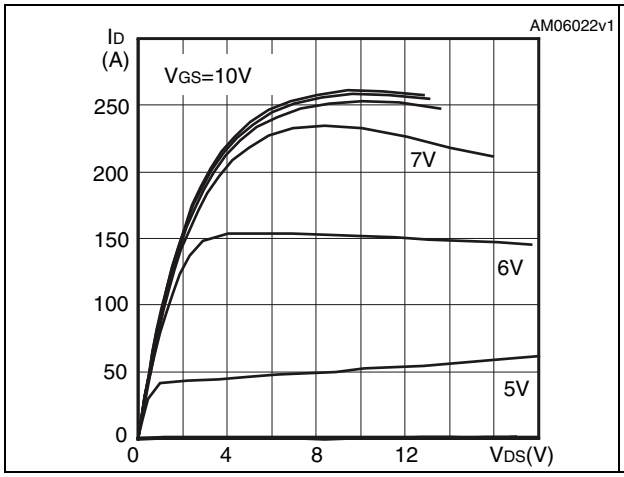


Figure 5. Transfer characteristics

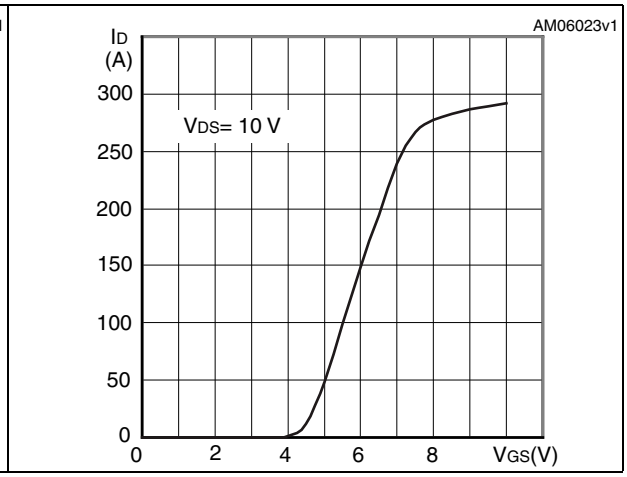


Figure 6. Normalized BV_{DSS} vs temperature

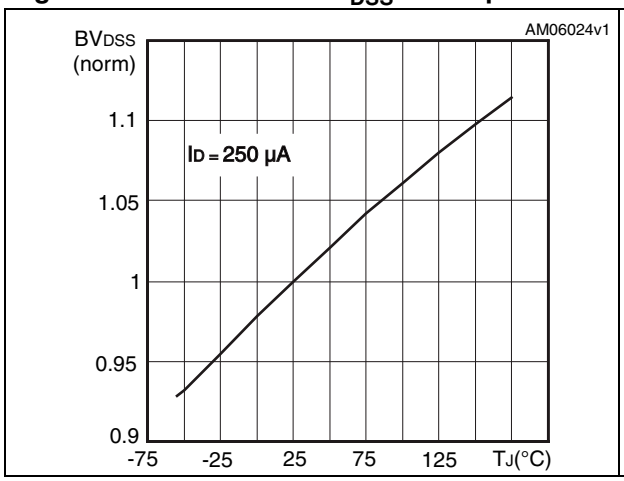


Figure 7. Static drain-source on-resistance

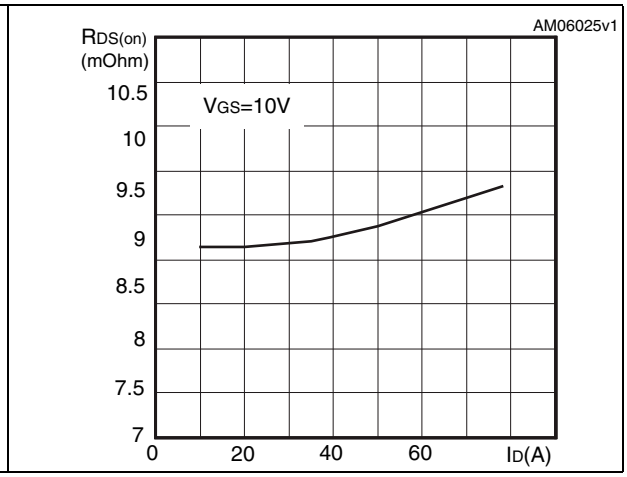


Figure 8. Gate charge vs gate-source voltage

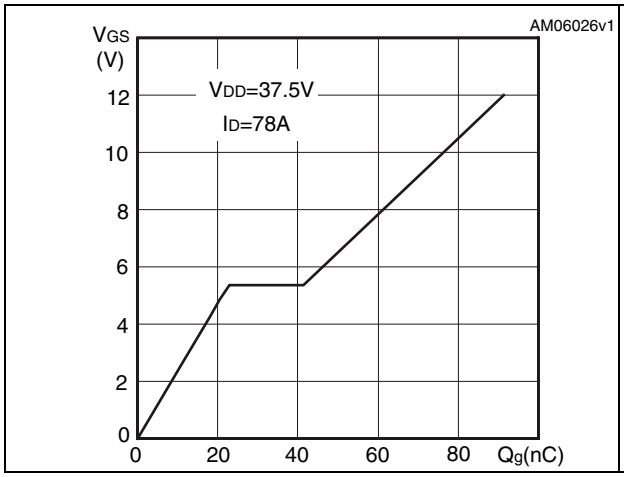


Figure 9. Capacitance variations

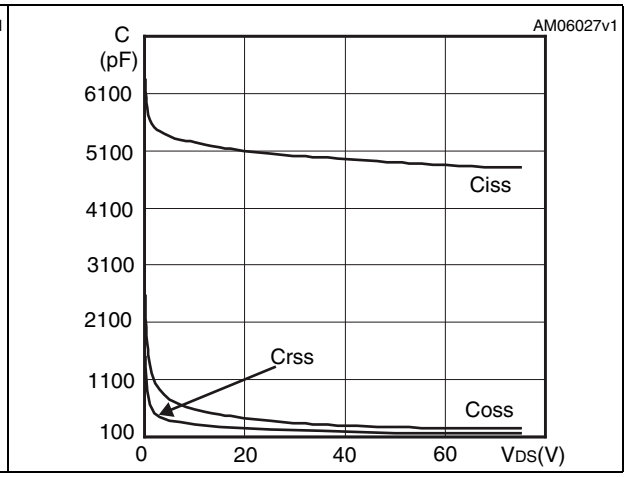


Figure 10. Normalized on-resistance vs temperature

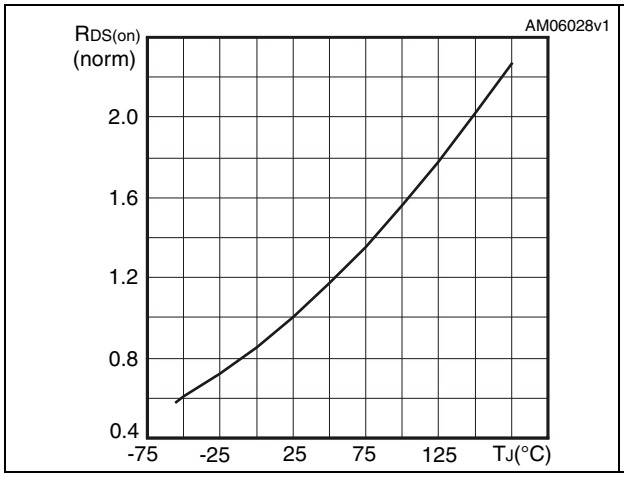


Figure 11. Normalized gate threshold voltage vs temperature

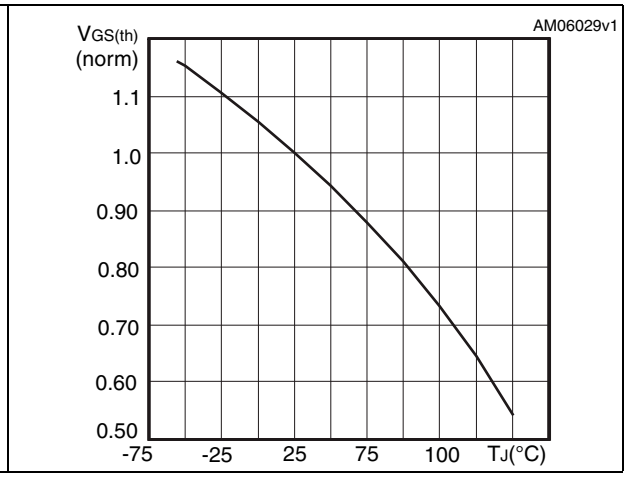
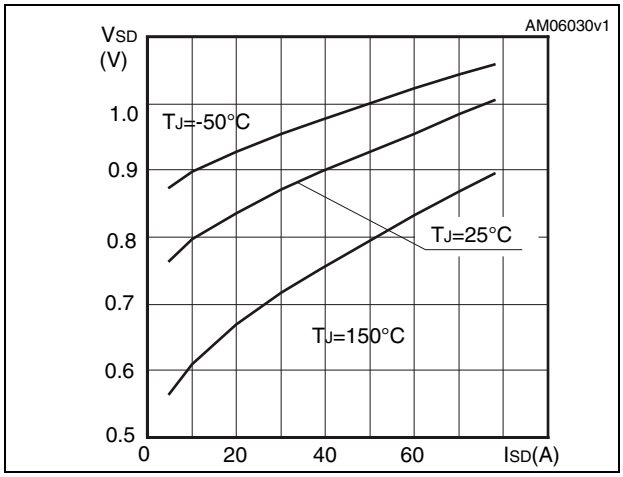


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

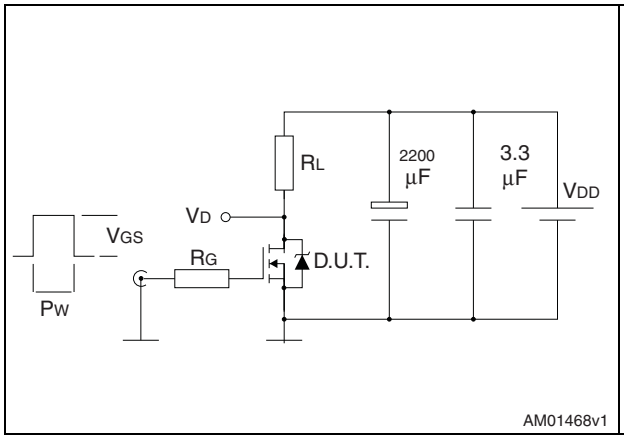


Figure 14. Gate charge test circuit

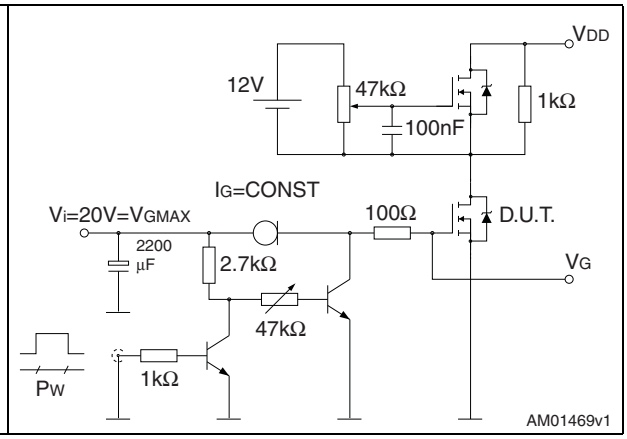


Figure 15. Test circuit for inductive load switching and diode recovery times

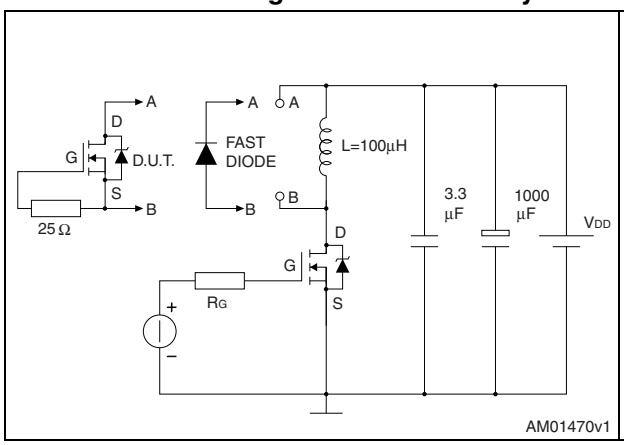


Figure 16. Unclamped inductive load test circuit

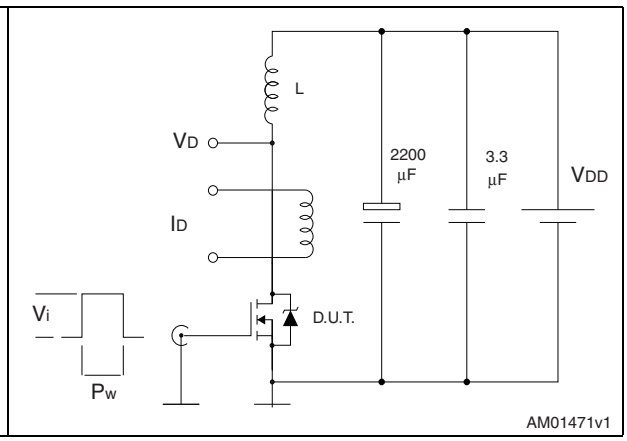


Figure 17. Unclamped inductive waveform

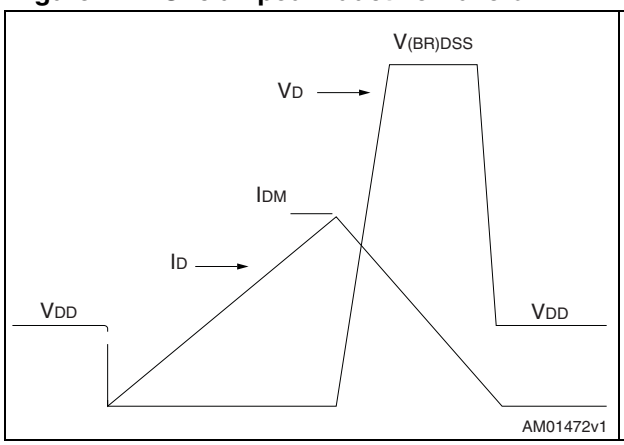
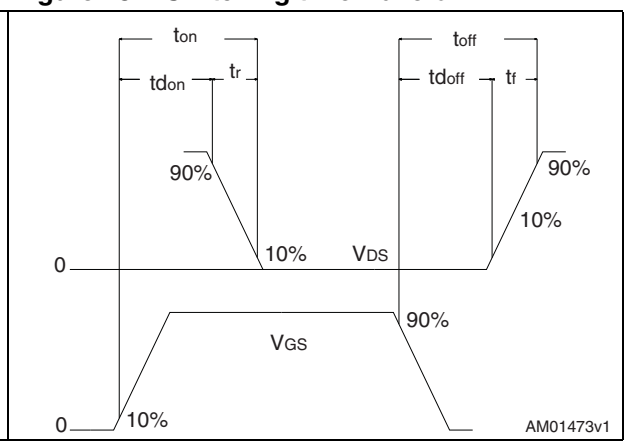


Figure 18. Switching time waveform



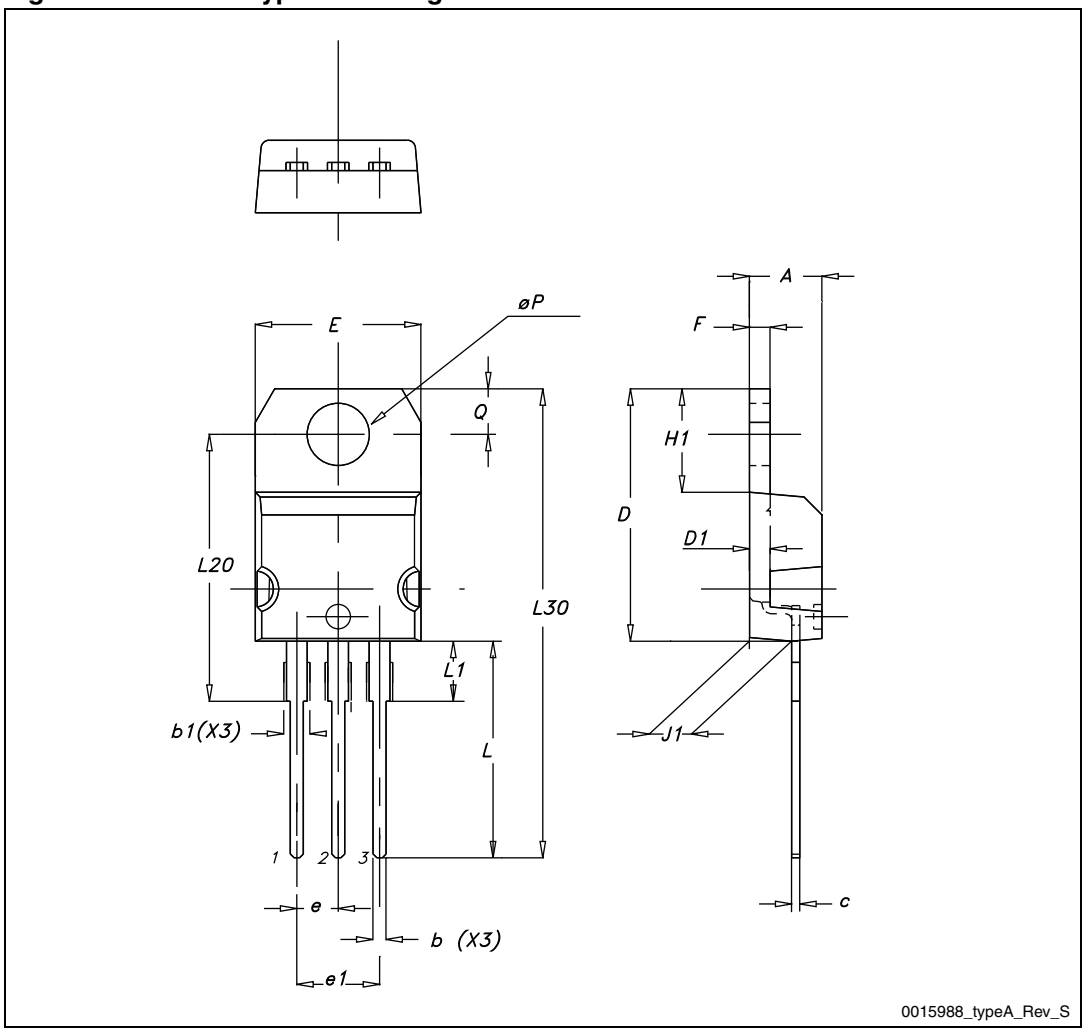
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
24-Jul-2012	1	First release.

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